

SEMICONDUCTOR

HGTG11N120CN, HGTP11N120CN, HGT1S11N120CNS

Data Sheet

December 2001

43A, 1200V, NPT Series N-Channel IGBT

The HGTG11N120CN, HGTP11N120CN, and WWW HGT1S11N120CNS are Non-Punch Through (NPT) IGBT designs. They are new members of the MOS gated high voltage switching IGBT family. IGBTs combine the best features of MOSFETs and bipolar transistors. This device has the high input impedance of a MOSFET and the low onstate conduction loss of a bipolar transistor.

The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as: AC and DC motor controls, power supplies and drivers for solenoids, relays and contactors.

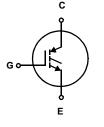
Formerly Developmental Type TA49291.

Ordering Information

PART NUMBER	PACKAGE	BRAND		
HGTG11N120CN	TO-247	G11N120CN		
HGTP11N120CN	TO-220AB	11N120CN		
HGT1S11N120CNS	TO-263AB	11N120CN		

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in Tape and Reel, i.e., HGT1S11N120CNS9A.

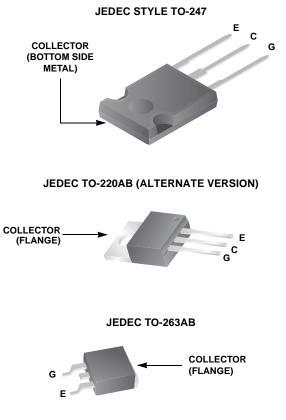
Symbol



Features

- 43A, 1200V, T_C = 25^oC
- 1200V Switching SOA Capability
- Short Circuit Rating
- Low Conduction Loss
- Avalanche Rated
- Thermal Impedance SPICE Model
 Temperature Compensating SABER™ Model
 www.fairchildsemi.com
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Packaging



FAIRCH	IILD SEMICONDU	ICTOR IGBT PRO	DUCT IS COVER	ED BY ONE OR M	ORE OF THE FO	LLOWING U.S. PA	TENTS
4,364,073	4,417,385	4,430,792	4,443,931	4,466,176	4,516,143	4,532,534	4,587,713
4,598,461	4,605,948	4,620,211	4,631,564	4,639,754	4,639,762	4,641,162	4,644,637
4,682,195	4,684,413	4,694,313	4,717,679	4,743,952	4,783,690	4,794,432	4,801,986
4,803,533	4,809,045	4,809,047	4,810,665	4,823,176	4,837,606	4,860,080	4,883,767
4,888,627	4,890,143	4,901,127	4,904,609	4,933,740	4,963,951	4,969,027	

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	HGTG11N120CN HGTP11N120CN HGT1S11N120CNS	UNITS
Collector to Emitter Voltage BV _{CES}	1200	V
Collector Current Continuous		
At $T_{C} = 25^{\circ}C$ I_{C25}	43	А
www.daAtshe≅4140%01	22	А
Collector Current Pulsed (Note 1) I _{CM}	80	А
Gate to Emitter Voltage ContinuousV _{GES}	±20	V
Gate to Emitter Voltage PulsedV _{GEM}	±30	V
Switching Safe Operating Area at T _J = 150 ^o C (Figure 2) SSOA	55A at 1200V	
Power Dissipation Total at $T_C = 25^{\circ}C$ P_D	298	W
Power Dissipation Derating T _C > 25 ^o C	2.38	W/ ^o C
Forward Voltage Avalanche Energy (Note 2)	80	mJ
Operating and Storage Junction Temperature Range	-55 to 150	°C
Maximum Lead Temperature for Soldering		
Leads at 0.063in (1.6mm) from case for 10s	300	°C
Package Body for 10s, see Tech brief 334	260	°C
Short Circuit Withstand Time (Note 3) at V_{GE} = 15V	8	μs
Short Circuit Withstand Time (Note 3) at V _{GE} = 12Vt _{SC}	15	μs

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- 1. Pulse width limited by maximum junction temperature.
- 2. $I_{CE} = 20A$, $L = 400\mu H$, $T_{J} = 25^{\circ}C$.
- 3. $V_{CE(PK)} = 840V$, $T_J = 125^{\circ}C$, $R_G = 10\Omega$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Collector to Emitter Breakdown Voltage	BV _{CES}	I _C = 250μA, V _{GE} = 0V		1200	-	-	V
Emitter to Collector Breakdown Voltage	BVECS	I _C = 10mA, V _{GE} = 0V		15	-	-	V
Collector to Emitter Leakage Current	ICES	V _{CE} = 1200V	$T_{C} = 25^{\circ}C$	-	-	250	μΑ
			T _C = 125 ⁰ C	-	250	-	μΑ
			T _C = 150 ⁰ C	-	-	3	mA
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C = 11A, V _{GE} = 15V	$T_{C} = 25^{\circ}C$	-	2.1	2.4	V
			T _C = 150 ⁰ C	-	2.8	3.5	V
Gate to Emitter Threshold Voltage	V _{GE(TH)}	$I_{C} = 90\mu A$, $V_{CE} = V_{GE}$		6.0	6.8	-	V
Gate to Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 20V$		-	-	±250	nA
Switching SOA	SSOA	$ \begin{array}{l} {T_{J}} = 150^{0}C, R_{G} = 10\Omega, V_{GE} = 15V, \\ {L} = 400\muH, V_{CE(PK)} = 1200V \end{array} $		55	-	-	A
Gate to Emitter Plateau Voltage	V _{GEP}	$I_{C} = 11A, V_{CE} = 600V$		-	10.4	-	V
On-State Gate Charge	Q _{G(ON)}	I _C = 11A, V _{CE} = 600V	V _{GE} = 15V	-	100	120	nC
			V _{GE} = 20V	-	130	150	nC

HGTG11N120CN, HGTP11N120CN, HGT1S11N120CNS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Current Turn-On Delay Time	^t d(ON)I	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	-	23	26	ns
Current Rise Time	t _{rl}		-	12	16	ns
Current Turn-Off Delay Time	^t d(OFF)I		-	180	240	ns
Current-Fall Time	t _{fl}		-	190	230	ns
Turn-On Energy (Note 4)	E _{ON1}		-	0.4	0.5	mJ
Turn-On Energy (Note 4)	E _{ON2}		-	0.95	1.3	mJ
Turn-Off Energy (Note 5)	E _{OFF}		-	1.3	1.6	mJ
Current Turn-On Delay Time	^t d(ON)I	$ \begin{array}{l} \text{IGBT and Diode at } T_J = 150^{\text{O}\text{C}} \\ \text{I}_{\text{CE}} = 11\text{A} \\ \text{V}_{\text{CE}} = 960\text{V} \\ \text{V}_{\text{GE}} = 15\text{V} \\ \text{R}_{\text{G}} = 10\Omega \\ \text{L} = 2\text{mH} \\ \end{array} \\ \hline \text{Test Circuit (Figure 18)} \\ \end{array} $	-	21	24	ns
Current Rise Time	t _{rl}		-	12	16	ns
Current Turn-Off Delay Time	^t d(OFF)I		-	210	280	ns
Current Fall Time	t _{fl}		-	340	400	ns
Turn-On Energy (Note 4)	E _{ON1}		-	0.45	0.6	mJ
Turn-On Energy (Note 4)	E _{ON2}		-	1.9	2.5	mJ
Turn-Off Energy (Note 5)	E _{OFF}		-	2.1	2.5	mJ
Thermal Resistance Junction To Case	R _{θJC}		-	-	0.42	°C/W

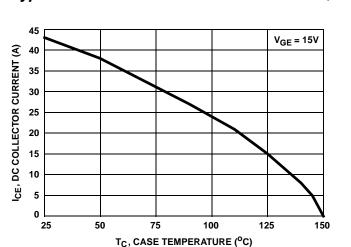
Electrical Specifications $T_{C} = 25^{\circ}C$, Unless Otherwise Specified (Continued)

NOTES:

W

4. Values for two Turn-On loss conditions are shown for the convenience of the circuit designer. E_{ON1} is the turn-on loss of the IGBT only. E_{ON2} is the turn-on loss when a typical diode is used in the test circuit and the diode is at the same T_J as the IGBT. The diode type is specified in Figure 18.

5. Turn-Off Energy Loss (E_{OFF}) is defined as the integral of the instantaneous power loss starting at the trailing edge of the input pulse and ending at the point where the collector current equals zero (I_{CE} = 0A). All devices were tested per JEDEC Standard No. 24-1 Method for Measurement of Power Device Turn-Off Switching Loss. This test method produces the true total Turn-Off Energy Loss.



Typical Performance Curves Unless Otherwise Specified

FIGURE 1. DC COLLECTOR CURRENT vs CASE TEMPERATURE

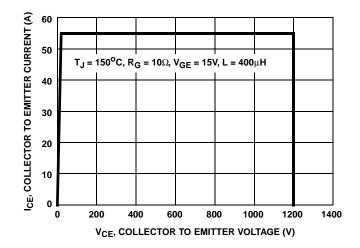
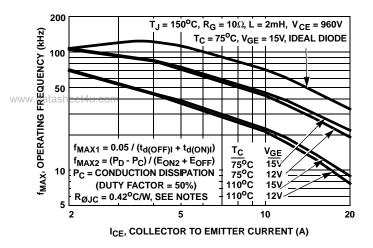


FIGURE 2. MINIMUM SWITCHING SAFE OPERATING AREA

Typical Performance Curves Unless Otherwise Specified (Continued)





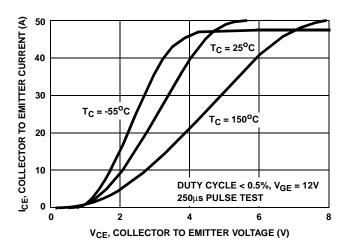
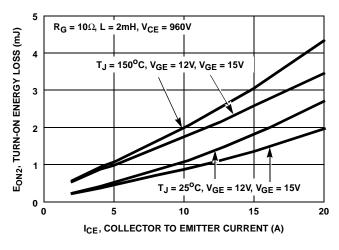
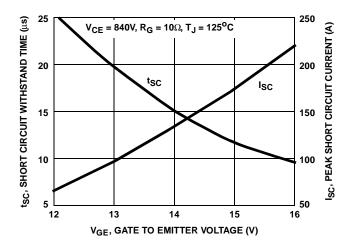


FIGURE 5. COLLECTOR TO EMITTER ON-STATE VOLTAGE









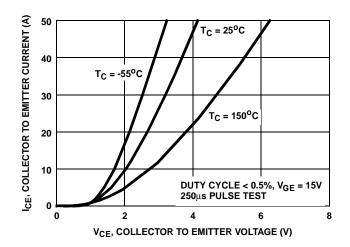
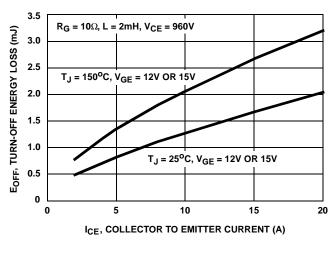
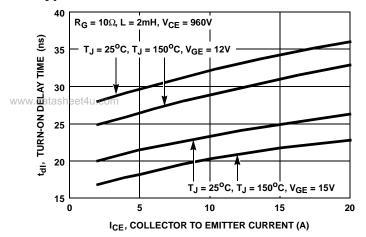


FIGURE 6. COLLECTOR TO EMITTER ON-STATE VOLTAGE

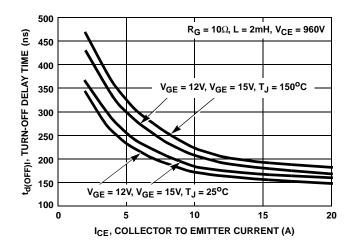




Typical Performance Curves Unless Otherwise Specified (Continued)









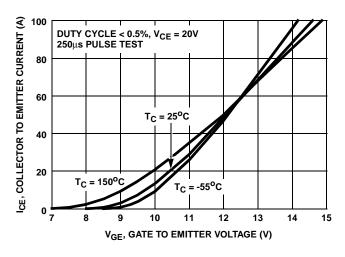
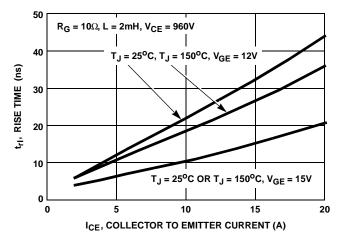
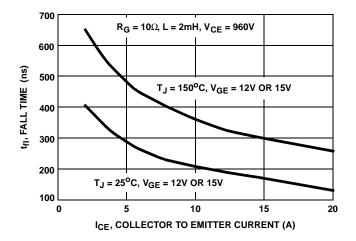


FIGURE 13. TRANSFER CHARACTERISTIC









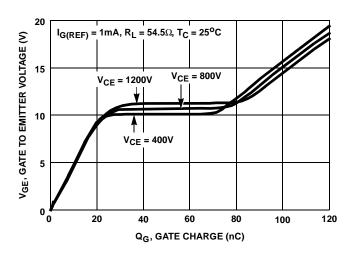
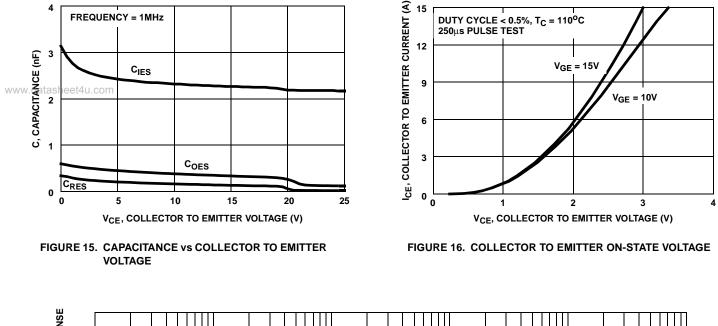


FIGURE 14. GATE CHARGE WAVEFORMS

Typical Performance Curves Unless Otherwise Specified (Continued)



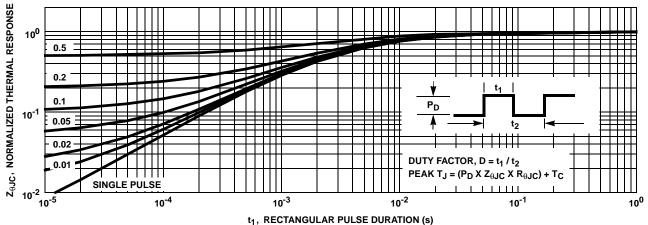


FIGURE 17. NORMALIZED TRANSIENT THERMAL RESPONSE, JUNCTION TO CASE

Test Circuit and Waveforms

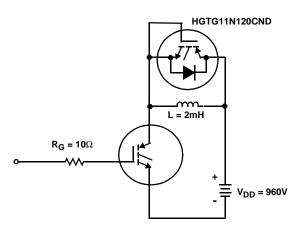


FIGURE 18. INDUCTIVE SWITCHING TEST CIRCUIT

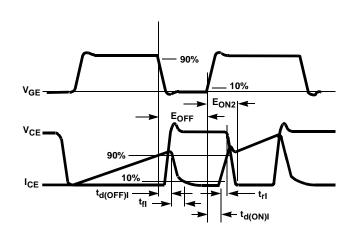


FIGURE 19. SWITCHING TEST WAVEFORMS

Handling Precautions for IGBTs

Insulated Gate Bipolar Transistors are susceptible to gate-insulation damage by the electrostatic discharge of energy through the devices. When handling these devices, care should be exercised to assure that the static charge built in the handler's body capacitance is not discharged through the device. With proper handling and application procedures, however, IGBTs are currently being extensively used in production by numerous equipment manufacturers in military, industrial and consumer applications, with virtually no damage problems due to electrostatic discharge. IGBTs can be handled safely if the following basic precautions are taken:

- Prior to assembly into a circuit, all leads should be kept shorted together either by the use of metal shorting springs or by the insertion into conductive material such as "ECCOSORBD™ LD26" or equivalent.
- 2. When devices are removed by hand from their carriers, the hand being used should be grounded by any suitable means for example, with a metallic wristband.
- 3. Tips of soldering irons should be grounded.
- 4. Devices should never be inserted into or removed from circuits with power on.
- Gate Voltage Rating Never exceed the gate-voltage rating of V_{GEM}. Exceeding the rated V_{GE} can result in permanent damage to the oxide layer in the gate region.
- 6. **Gate Termination** The gates of these devices are essentially capacitors. Circuits that leave the gate open-circuited or floating should be avoided. These conditions can result in turn-on of the device due to voltage buildup on the input capacitor due to leakage currents or pickup.
- 7. **Gate Protection** These devices do not have an internal monolithic Zener diode from gate to emitter. If gate protection is required an external Zener is recommended.

Operating Frequency Information

Operating frequency information for a typical device (Figure 3) is presented as a guide for estimating device performance for a specific application. Other typical frequency vs collector current (I_{CE}) plots are possible using the information shown for a typical unit in Figures 5, 6, 7, 8, 9 and 11. The operating frequency plot (Figure 3) of a typical device shows f_{MAX1} or f_{MAX2} ; whichever is smaller at each point. The information is based on measurements of a typical device and is bounded by the maximum rated junction temperature.

 f_{MAX1} is defined by $f_{MAX1} = 0.05/(t_{d(OFF)I} + t_{d(ON)I})$. Deadtime (the denominator) has been arbitrarily held to 10% of the on-state time for a 50% duty factor. Other definitions are possible. $t_{d(OFF)I}$ and $t_{d(ON)I}$ are defined in Figure 19. Device turn-off delay can establish an additional frequency limiting condition for an application other than T_{JM} . $t_{d(OFF)I}$ is important when controlling output ripple under a lightly loaded condition.

 f_{MAX2} is defined by f_{MAX2} = (P_D - P_C)/(E_OFF + E_ON2). The allowable dissipation (P_D) is defined by P_D = (T_{JM} - T_C)/R_{\theta JC}. The sum of device switching and conduction losses must not exceed P_D. A 50% duty factor was used (Figure 3) and the conduction losses (P_C) are approximated by P_C = (V_{CE} \times I_{CE})/2.

 E_{ON2} and E_{OFF} are defined in the switching waveforms shown in Figure 19. E_{ON2} is the integral of the instantaneous power loss ($I_{CE} \times V_{CE}$) during turn-on and E_{OFF} is the integral of the instantaneous power loss ($I_{CE} \times V_{CE}$) during turn-off. All tail losses are included in the calculation for E_{OFF} ; i.e., the collector current equals zero ($I_{CE} = 0$).